# onsemi

## <u>Silicon Carbide (SiC)</u> <u>Schottky Diode</u> – EliteSiC, 20 A, 650 V, D2, TO-220-2L

### FFSP2065B-F085

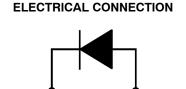
Silicon Carbide (SiC) Schottky Diodes use a completely new technology that provides superior switching performance and higher reliability compared to Silicon. No reverse recovery current, temperature independent switching characteristics, and excellent thermal performance sets Silicon Carbide as the next generation of power semiconductor. System benefits include highest efficiency, faster operating frequency, increased power density, reduced EMI, and reduced system size and cost.

#### Features

- Max Junction Temperature 175°C
- Avalanche Rated 94 mJ
- High Surge Current Capacity
- Positive Temperature Coefficient
- Ease of Paralleling
- No Reverse Recovery / No Forward Recovery
- AEC-Q101 Qualified and PPAP Capable
- These Devices are Pb–Free, Halogen Free/BFR Free and are RoHS Compliant

#### Applications

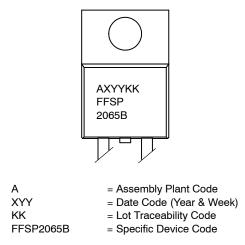
- Automotive HEV–EV Onboard Chargers
- Automotive HEV-EV DC-DC Converters



1. Cathode 2. Anode



#### MARKING DIAGRAM



#### ORDERING INFORMATION

See detailed ordering and shipping information in the package dimensions section on page 2 of this data sheet.

#### **ABSOLUTE MAXIMUM RATINGS**

(T<sub>C</sub> = 25°C, Unless otherwise specified)

Symbol	Parameter		FFSP2065B-F085	Unit
V <sub>RRM</sub>	Peak Repetitive Reverse Voltage		650	V
E <sub>AS</sub>	Single Pulse Avalanche Energy (Note 1)		94	mJ
١ <sub>F</sub>	Continuous Rectified Forward Current @ T <sub>C</sub>	< 141°C	20	А
	Continuous Rectified Forward Current @ T <sub>C</sub>	22.5		
1, 10100	Non-Repetitive Peak Forward Surge Cur- rent	T <sub>C</sub> = 25°C, 10 μs	882	А
		T <sub>C</sub> = 150°C, 10 μs	798	
I <sub>F, SM</sub>	Non-Repetitive Forward Surge Current	Half-Sine Pulse, $t_p = 8.3 \text{ ms}$	84	A
P <sub>tot</sub>	Power Dissipation	T <sub>C</sub> = 25°C	150	W
		T <sub>C</sub> = 150°C	25	
T <sub>J</sub> , T <sub>STG</sub>	Operating and Storage Temperature Range		-55 to +175	°C

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected. 1.  $E_{AS}$  of 94 mJ is based on starting  $T_J$  = 25°C, L = 0.5 mH,  $I_{AS}$  = 19.4 A, V = 50 V.

#### **THERMAL CHARACTERISTICS**

Symbol	Parameter	Ratings	Unit
$R_{\thetaJC}$	Thermal Resistance, Junction to Case, Max.	1.0	°C/W

#### **ELECTRICAL CHARACTERISTICS** $T_C = 25^{\circ}C$ unless otherwise noted

Symbol	Parameter	Test Conditions	Min.	Тур.	Max.	Unit
V <sub>F</sub>	Forward Voltage	$I_{F} = 20 \text{ A}, \text{ T}_{C} = 25^{\circ}\text{C}$	-	1.38	1.7	V
		I <sub>F</sub> = 20 A, T <sub>C</sub> = 125°C	-	1.6	2.0	1
		I <sub>F</sub> = 20 A, T <sub>C</sub> = 175°C	-	1.72	2.4	1
I <sub>R</sub>	Reverse Current	$V_{R} = 650 \text{ V}, \text{ T}_{C} = 25^{\circ}\text{C}$	-	0.5	40	μΑ
		$V_{R} = 650 \text{ V}, \text{ T}_{C} = 125^{\circ}\text{C}$	-	1	80	1
		$V_{R} = 650 \text{ V}, \text{ T}_{C} = 175^{\circ}\text{C}$	-	2	160	1
$Q_{C}$	Total Capacitive Charge	V = 400 V	-	51	-	nC
С	Total Capacitance	V <sub>R</sub> = 1 V, f = 100 kHz	-	866	-	pF
		V <sub>R</sub> = 200 V, f = 100 kHz	-	80	-	1
		V <sub>R</sub> = 400 V, f = 100 kHz	-	70	-	1

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

#### PACKAGE MARKING AND ORDERING INFORMATION

Part Number	Top Mark	Package	Packing Method	Reel Size	Tape Width	Quantity
FFSP2065B-F085	FFSP2065B	TO-220-2LD	Tube	N/A	N/A	50 Units

#### FFSP2065B-F085

#### TYPICAL CHARACTERISTICS TJ = 25°C UNLESS OTHERWISE NOTED

P<sub>TOT</sub>, POWER DISSIPATION (W)

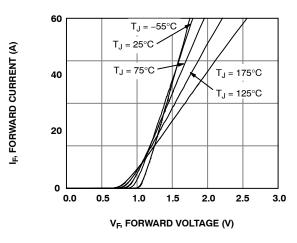


Figure 1. Forward Characteristics

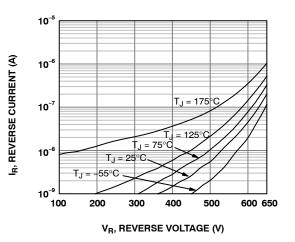
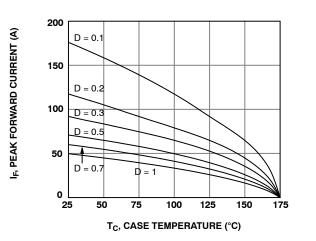
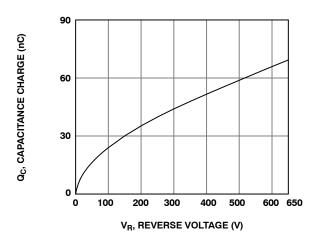


Figure 2. Reverse Characteristics



**Figure 3. Current Derating** 





180 120 60 0 25 50 75 100 125 150 175 T<sub>C</sub>, CASE TEMPERATURE (°C)

Figure 4. Power Dissipation

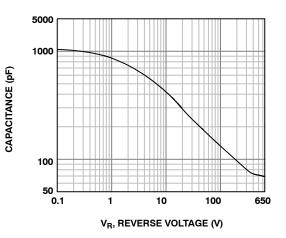
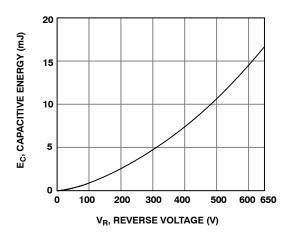
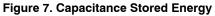


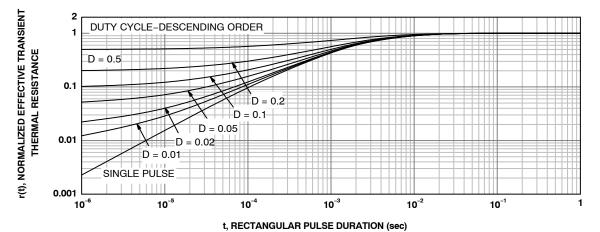
Figure 6. Capacitance vs. Reverse Voltage

#### FFSP2065B-F085

**TYPICAL CHARACTERISTICS**  $T_J = 25^{\circ}C$  UNLESS OTHERWISE NOTED (CONTINUED)









#### TEST CIRCUIT AND WAVEFORMS

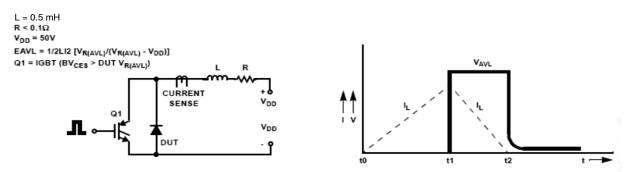
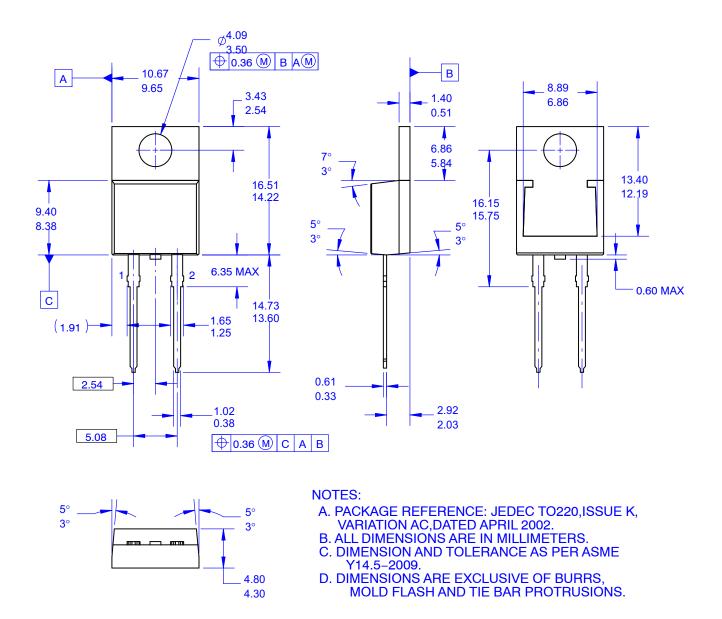


Figure 9. Unclamped Inductive Switching Test Circuit & Waveform



TO-220-2LD CASE 340BB ISSUE O

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